

**AMENDMENTS TO THE CLAIMS**

Please replace the claims, including all prior versions, with the listing of claims below.

**Listing of Claims:**

1. (Currently amended) ~~Method~~A method for masking first recesses (1) in a structure (4) having webs (4) with a high aspect ratio, comprising a set of recesses (1, 2) having different aspect ratios, ~~in particular a semiconductor structure, having the following steps comprising:~~
  - ~~applying a filling layer (5) is applied to the structure (1, 2, 4), with the filling layer (5) being applied over a fixed distance beyond the webs (4) in such a way that a cavity (6) is formed in the first recesses (1) having a high aspect ratio;~~
  - ~~removing the filling layer (5) is removed by means of a planar removal process into the area of the cavity (6) with the filling layer (5) being removed to a defined distance above the surface of the webs (4);~~
  - ~~removing the filling layer (5) is removed in an etching process, with the etching process also attacking in the cavity (6) and, owing to the cavity (6), the filling layer (5) being removed more quickly from the first recess (1) than from recesses (2) without a cavity (6), and with the etching process being stopped after removal of the filling layer (5) from the first recess (1), with the defined distance being chosen selected such that the webs (4) are not underetched in the area of a recess (2) with a low aspect ratio during the etching process.~~
2. (Currently amended) ~~Method~~The method according to Claim 1, characterized in that wherein an isotropic etching method is used as the etching method.
3. (Currently amended) ~~Method~~The method according to one of Claims 1 or 2, characterized in that claim 1, wherein the structure (1, 2, 4) has the webs (4), and in that a sacrificial layer (12) is applied to the surface of the webs (4), before the application of the filling layer (5).

4. (Currently amended) ~~Method~~ The method according to one of Claims 1 to 3, characterized in that claim 1, wherein a chemical/mechanical polishing method is used as the a planar removal process.
5. (Currently amended) ~~Method~~ The method according to Claim 4, characterized in that wherein the defined distance is chosen to be greater than twice the a maximum thickness ( $\beta$ ) of the filling material (5) between the cavity (6) and the structure (4, 3).
6. (Currently amended) ~~Method~~ The method according to one of Claims 1 to 5, characterized in that claim 1, wherein the structure (1, 2, 4) is formed from a silicon wafer (3).
7. (Currently amended) ~~Method~~ The method according to one of Claims 1 to 6, characterized in that claim 1, wherein a silicon oxide is deposited as the filling layer (5), using a TEOS process.
8. (Currently amended) ~~Method~~ The method according to one of Claims 1 to 7, characterized in that claim 1, wherein silicon oxide is deposited as the sacrificial layer (12).
9. (Currently amended) ~~Method~~ The method according to one of Claims 1 to 8, characterized in that claim 1, wherein the filling layer (5) is applied over a recess (2) with a low aspect ratio to above thea height of the cavity (6).